
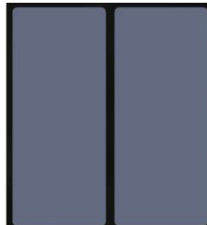



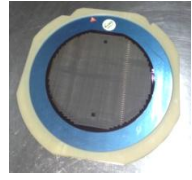





DEVICE TYPE: 100V Schottky Barrier Diode(High ESD)

CHIP LAY-OUT	CHIP INFO	DIMENSION / DATA		
<div style="display: flex; justify-content: space-around;"> <div style="text-align: center;"> <p>Single die</p>  </div> <div style="text-align: center;"> <p>Dual die</p>  </div> </div> <div style="text-align: center; margin-top: 20px;"> <p>TOP VIEW</p>  </div> <div style="text-align: center; margin-top: 20px;"> <p>SIDE VIEW</p>  </div>	V_{RWM}	100V		
	I_{FAV}	1A~120A		
	T_{JMAX}	150~175°C		
	WAFER SIZE	150 ± 0.3 mm		
	CHIP SIZE	28mil~300mil		
	CHIP THICKNESS	6~11 mils		
	SCRIBE LINE WIDTH	4 mils		
	METALLIZATION			
	- Top Metal		>70mil	≤70mil
	Ag	36000Å	48000Å	
	Au	6500Å		
	Al	73000Å		
	- Back Metal		>70mil	≤70mil
	Ag	11000Å	17000Å	
Au	4000Å			
ESD Capability	Minimum Electro-Static Discharge resistance to voltage			
	JEDEC Standard	>8	kv	
	IEC-61000-4-2 Standard	>8		
Delivery	Wafer (6 inch) 	Dies with tape 	Dies in bottle (≤70mil) 	

YIELD CUT-OFF: 95%

WAFER MANUFACTURER: Li-ON Microelectronics

LOCATION: Hangzhou, China

Update:2018-6-4


DEVICE TYPE: 100V Schottky Barrier Diode(High ESD)

ELECTRICAL RATINGS & CHARACTERISTICS $T_J > 150^\circ\text{C}$ ($T_A = 25^\circ\text{C}$, UNLESS OTHERWISE NOTED)								
SYMBOL	CHIP SIZE (mil)	CONTACT SIZE(mil)	I_{FAV} (A)	Device	RS(A)	IFSM(A)	V_{FMAX} (V)	I_{RMAX} (uA)
Single die	24.4	18.1*18.1	1		1	20		
	28	20*20	1	S1031A	1	25	0.81	5
	32	24*24	1	S1039A	1	30	0.86	10
	35	27*27	1	S1189A	1	35	0.83	10
	40	32*32	2	S1088A	1	40	0.87	10
	45	37*37	2	S1104A	1	50	0.81	10
	50	42*42	3	S1198A	2	60	0.85	10
	53	43.5*43.5	3	S1108A	2	80	0.81	10
	60	51.5*51.5	3	S1109A	2	100	0.77	10
	63	54*54	5	S1113A	2	120	0.83	10
	70	61*61	5	S1110A	2	150	0.77	10
	78	69*69	8	S1134A	2	180	0.84	10
	88	79*79	10	S1140A	2	200	0.82	10
	98	89.2*89.2	15	S1249A	2	250	0.82	10
	105	96.2*96.2	15		2	275		
	120	111.2*111.2	15		3	275		
	130	120.8*120.8	20	S1148A	3	275	0.77	20
	150	141.7*141.7	30	S1149A	3	275	0.77	20
	175	166.7*166.7	40		3	275		
	200	190.5*190.5	50	S1392A	3	275	0.77	30
250	237*237	80		3	275			
275	266.7*266.7	100		3	275			
300	287*287	120		3	275			
Dual die	86	36.15*78*2	2*5	S1111A	2	120	0.82	10
	97	40.65*88*2	2*5	S1252A	2	150	0.8	10
	102	44.25*94*2	2*10	S1166A	2	160	0.92	10
	112	48.25*103*2	2*10	S1250A	2	180	0.85	10
	122	54.25*114*2	2*10	S1207A	2	200	0.82	10
	141	63.25*132.5*2	2*15	S1218A	3	250	0.82	10
	170	77.25*161*2	2*20		3	275		


DEVICE TYPE: 100V Schottky Barrier Diode(High ESD)

ELECTRICAL RATINGS & CHARACTERISTICS $T_J > 175^\circ\text{C}$ ($T_A = 25^\circ\text{C}$, UNLESS OTHERWISE NOTED)								
SYMBOL	CHIP SIZE (mil)	CONTACT SIZE(mil)	I_{FAV} (A)	Device	RS(A)	IFSM(A)	V_{FMAX} (V)	I_{RMAX} (μ A)
Single die	24.4	18.1*18.1	1		1	20		
	28	20*20	1	S2031A	1	25	0.83	5
	32	24*24	1		1	30		
	35	27*27	1		1	35		
	40	32*32	2		1	40		
	45	37*37	2	S2104A	1	50	0.82	5
	50	42*42	3	S2198A	2	60	0.85	5
	53	43.5*43.5	3	S2108A	2	80	0.82	5
	60	51.5*51.5	3	S2109A	2	100	0.8	5
	63	54*54	5		2	120		
	70	61*61	5	S2110A	2	150	0.8	5
	78	69*69	8	S2134A	2	180	0.85	5
	88	79*79	10	S2140A	2	200	0.82	5
	98	89.2*89.2	15		2	250		
	105	96.2*96.2	15	S2137A	2	275	0.83	5
	120	111.2*111.2	15	S2138A	3	275	0.8	5
	130	120.8*120.8	20	S2148A	3	275	0.8	5
	150	141.7*141.7	30	S2149A	3	275	0.82	5
	175	166.7*166.7	40	S2231A	3	275	0.82	5
	200	190.5*190.5	50		3	275		
250	237*237	80		3	275			
275	266.7*266.7	100	S2292A	3	275	0.75	20	
300	287*287	120	S2210A	3	275	0.8	30	
Dual die	86	36.15*78*2	2*5	S2111A	2	120	0.85	5
	97	40.65*88*2	2*5	S2252A	2	150	0.82	5
	102	44.25*94*2	2*10	S2166A	2	160	0.93	5
	112	48.25*103*2	2*10	S2255A	2	180	0.85	5
	122	54.25*114*2	2*10	S2207A	2	200	0.82	5
	141	63.25*132.5*2	2*15		3	250		
	170	77.25*161*2	2*20		3	275		